THIN FILM TRANSISTOR MATRIX AND ITS MANUFACTURE

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Abstract of **JP4334061**

PURPOSE:To obtain a thin film transistor matrix having a structure wherein the short circuit between data bus lines and gate bus lines and the disconnection of the gate bus lines are not generated. CONSTITUTION:The following are provided; a transparent insulative substrate 1, a transparent insulative layer 3 covering the substrate 1, and a plurality of parallel data bus lines 6 buried in the insulative layer 3 in the manner in which the height of the surface becomes nearly equal to the height of the surface of the insulative layer 3. A device is constituted of the following; a drain electrode 7 and a source electrode 8 laminated in order on the transparent insulative layer 3, an operating semiconductor layer 10, gate insulating layers 11, 12, a gate electrode 13, and a thin film transistor matrix having a plurality of parallel gate bus lines 14 perpendicularly intersecting a plurality of the parallel data bus lines 6.